



# DCR2040L42

# **Phase Control Thyristor**

DS5960-3 December 2013 (LN31164)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

# **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR2040L42 DCR2040L40 DCR2040L35	4200 4000 3500	$\begin{split} &T_{\nu j} = \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ &I_{DRM} = I_{RRM} = 200\text{mA}, \\ &V_{DRM}, V_{RRM} \ t_p = 10\text{ms}, \\ &V_{DSM} \ \& \ V_{RSM} = \\ &V_{DRM} \ \& \ V_{RRM} + 100V \\ &\text{respectively} \end{split}$
_		

Lower voltage grades available.

# **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR2040L42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

# **KEY PARAMETERS**

$V_{DRM}$	4200V
$I_{T(AV)}$	2040A
I <sub>TSM</sub>	29000A
dV/dt*	1500V/µs
dl/dt	400A/μs

# \* Higher dV/dt selections available

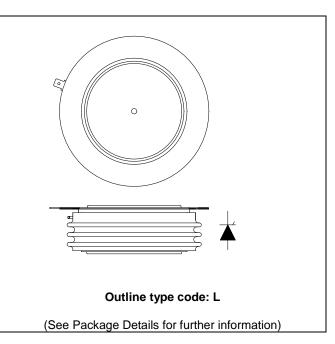


Fig. 1 Package outline



# **CURRENT RATINGS**

# T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	2040	А
I <sub>T(RMS)</sub>	RMS value	-	3204	А
I <sub>T</sub>	Continuous (direct) on-state current	-	2965	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	29	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	4.2	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{\text{th(j-c)}}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0117	°C/W
		Single side cooled	Anode DC	-	0.0187	°C/W
			Cathode DC	-	0.0329	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 37kN	Double side	-	0.0025	°C/W
		(with mounting compound)	Single side	-	0.005	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
Fm	Clamping force			33.0	41.0	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	200	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	-	1500	V/µs
dI/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	200	A/μs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V <sub>T(TO)</sub>	Threshold voltage – Low level	500A to 2000A at T <sub>case</sub> = 125	5°C	-	0.9	V
	Threshold voltage – High level	2000A to 7000A at T <sub>case</sub> = 125°C		-	1.08	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2000A at T <sub>case</sub> = 125°C		-	0.36	mΩ
	On-state slope resistance – High level	2000A to 7000A at T <sub>case</sub> = 125°C		-	0.265	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ $\mu$ s,		250	500	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt - 1A/\mu s$ ,		1000	3000	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	Α
lμ	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I <sub>T</sub> = 5A	-	300	mA



# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	350	mA
$I_{\mathrm{GD}}$	Gate non-trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	10	mA

### **CURVES**

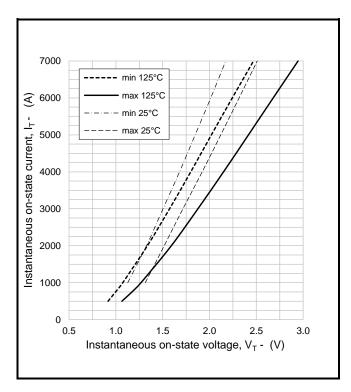


Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION** 

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.137154

B = 0.132631

C = 0.000248

D = -0.001126

these values are valid for  $T_j$  = 125°C for  $I_T$  100A to 7000A

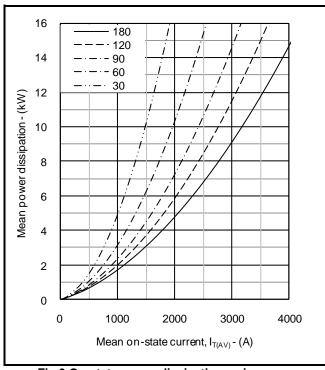


Fig.3 On-state power dissipation - sine wave

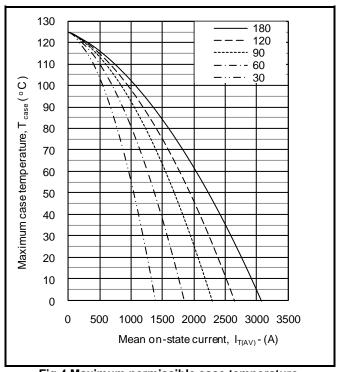


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

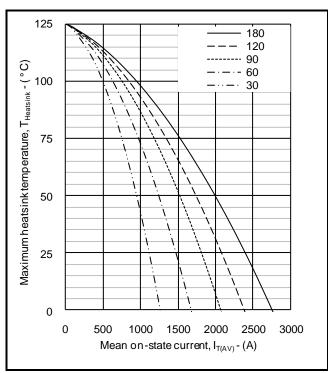


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

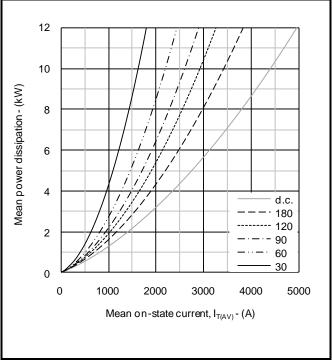


Fig.6 On-state power dissipation - rectangular wave

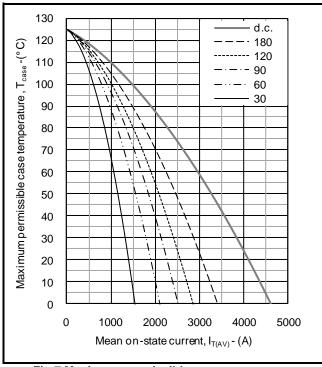


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

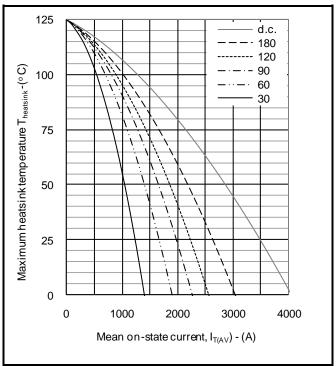
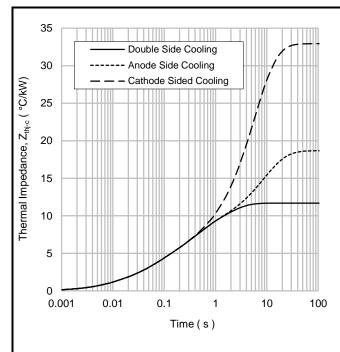


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	0.8342	2.6074	4.2073	4.041
	T <sub>i</sub> (s)	0.008639	0.0533503	0.3309504	1.612
Anode side cooled	R <sub>i</sub> (°C/kW)	0.9647	2.8312	4.9433	9.909
	T <sub>i</sub> (s)	0.0096096	0.0627037	0.4198958	8.908
Cathode side cooled	R <sub>i</sub> (°C/kW)	0.9285	2.9366	2.3581	26.683
	T <sub>i</sub> (s)	0.0093033	0.0621535	0.3092235	5.835

$$Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

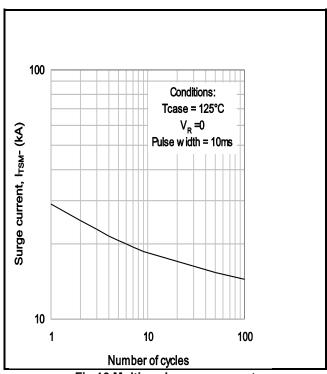
Tables show the increments of thermal resistance  $R_{\text{th}(j-c)}$  when the device operates at conduction angles other than d.c.

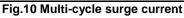
Double side cooling					
	$\Delta Z_{th}(z)$				
θ°	sine.	rect.			
180	1.45	0.98			
120	1.68	1.40			
90	1.93	1.64			
60	2.16	1.90			
30	2.34	2.19			

_	Anode Side	Cooling	
	$\Delta Z_{th}$ (z)		
θ°	sine.	rect.	
180	1.43	0.97	
120	1.66	1.39	
90	1.90	1.62	
60	2.12	1.88	
30	2.30	2.15	
15	2.27	2.20	

Cathode Sided Cooling			
	$\Delta Z_{th}(z)$		
θ°	sine.	rect.	
180	1.44	0.97	
120	1.66	1.39	
90	1.91	1.63	
60	2.14	1.89	
30	2.31	2.17	
4	0.00	0.04	

Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)





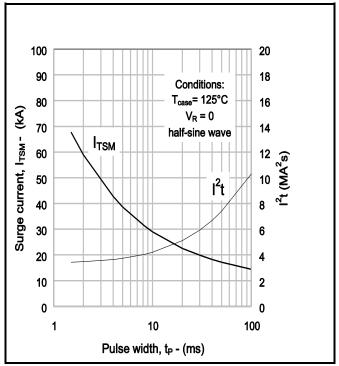


Fig.11 Single-cycle surge current

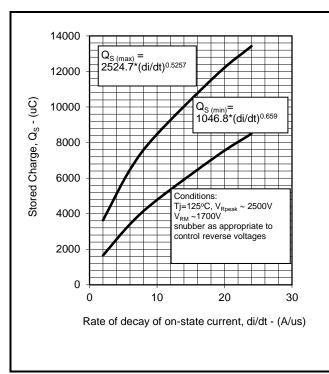


Fig.12 Reverse recovery charge

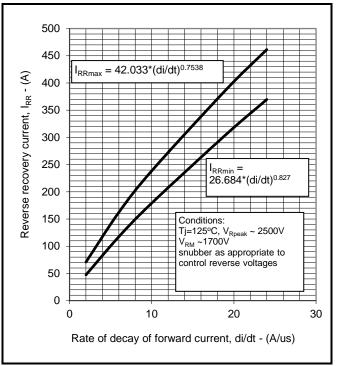


Fig.13 Reverse recovery current

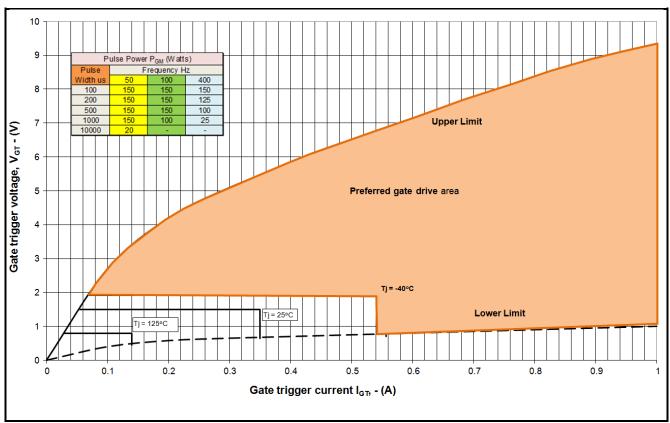


Fig14 Gate Characteristics

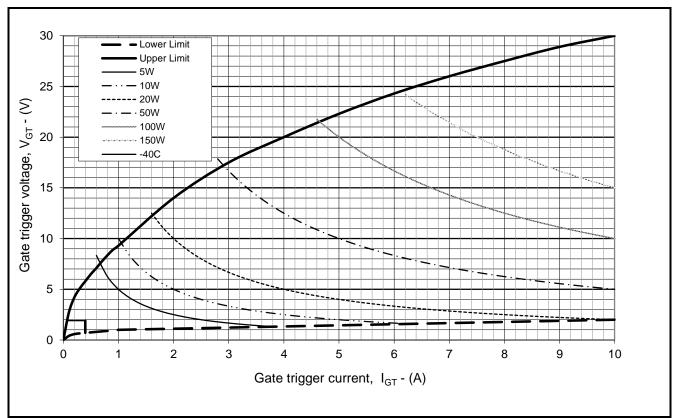


Fig. 15 Gate characteristics





### PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

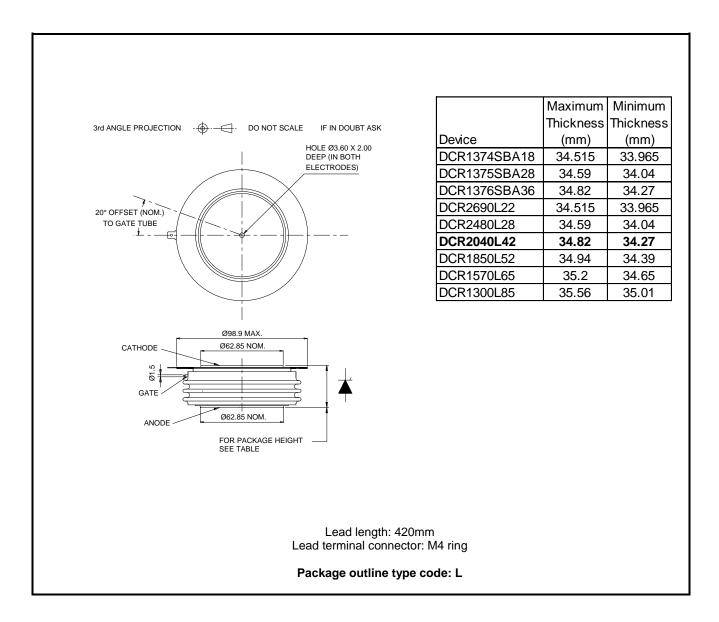


Fig.16 Package outline





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